Supporting Information

Low-temperature facile solution-processed gate dielectric and active channel for oxide thin film transistors

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The performances of TFTs transfer were demonstrated in figure S1.

**Figure S1** Transfer performances of the samples. The annealing temperatures of them are (a) 220°C, (b) 240°C, (c) 260°C, (d) 280°C and (e) 300°C.